



#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	20.5mΩ @ V <sub>GS</sub> = 10V	8.3A
30V	30mΩ @ V <sub>GS</sub> = 4.5V	7.4A

## **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

### **Features and Benefits**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
   A listing can be found at

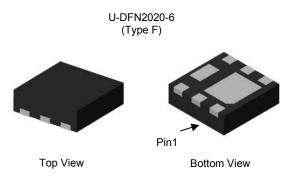
https://www.diodes.com/products/automotive/automotive-products/.

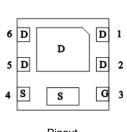
 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

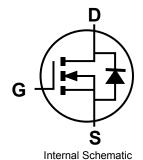
https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)







Pinout Bottom View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3025LFDF-7	U-DFN2020-6 (Type F)	3000/Tape & Reel
DMN3025LFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



# **Marking Information**

Site1



S6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2017	20	18	2019	2020	20	21	2022	2023	20	24	2025
Code	Е	F	F	G	Н		I	J	K		_	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



S6 = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: 0 = 2020)
Y = Wook (ex: 0 = 2020)

W = Week (ex: a = week 27; z represents week 52 and 53)

X = Internal code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026
Code	9	0	1	2	3	4	5	6

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Y	Z



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) / _ = 40\/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	8.3 6.6	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	9.9 7.9	А
Maximum Continuous Body Diode Forward Curre	nt (Note 6)		I <sub>S</sub>	3	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	I <sub>DM</sub>	40	Α		
Avalanche Current (L = 0.1mH) (Note 7)	I <sub>AS</sub>	15	Α		
Avalanche Energy (L = 0.1mH) (Note 7)		Eas	11	mJ	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Dawar Dissination (Note 5)	T <sub>A</sub> = +25°C	Б	0.66	W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	$P_{D}$	0.42	VV	
Thermal Decistance Junction to Ambient (Note 5)	Steady State	Б	173	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{\theta JA}$	133	C/VV	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	Б	2.1	W	
Total Power Dissipation (Note o)	T <sub>A</sub> = +70°C	$P_{D}$	1.3		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Б	62	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	43	C/VV	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{ heta JC}$	9.4	°C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	$BV_{DSS}$	30		_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	1	2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		
Static Drain-Source On-Resistance				20.5	mΩ	$V_{GS} = 10V, I_D = 7A$		
Static Dialii-Source Oil-Resistance	R <sub>DS(ON)</sub>	_	_	30	11122	$V_{GS} = 4.5V, I_D = 7A$		
Diode Forward Voltage	$V_{SD}$	_	0.70	1.0	V	$V_{GS} = 0V, I_{S} = 1A$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C <sub>iss</sub>		641	_		15)()(		
Output Capacitance	Coss		66	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>		50	_		1 - 1.0WH 12		
Gate Resistance	$R_g$	_	2.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg		6	_				
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	13.2	_	nC	\/ - 45\/   - 400		
Gate-Source Charge	Qgs	_	1.7	_	IIC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 10A		
Gate-Drain Charge	$Q_{gd}$	_	2.2	_				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.3	_				
Turn-On Rise Time	t <sub>R</sub>	_	4.4	_		V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	1	22.3	_	ns	$R_G = 6\Omega$ , $I_D = 1A$		
Turn-Off Fall Time	$t_{F}$	_	5.3	_				
Reverse Recovery Time	t <sub>RR</sub>	_	11.4	_	ns	I <sub>F</sub> = 11A, di/dt = 100A/μs		
Reverse Recovery Charge	Q <sub>RR</sub>		8.2		nC	I <sub>F</sub> = 11A, di/dt = 100A/μs		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

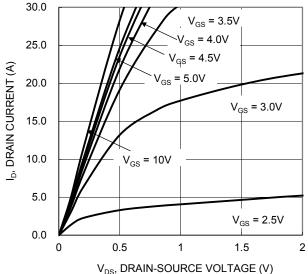
<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

<sup>7.</sup>  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

<sup>8.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>9.</sup> Guaranteed by design. Not subject to product testing.





V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic

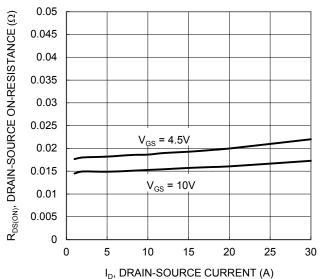


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

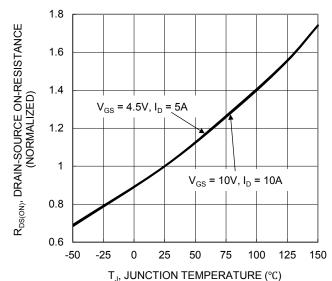


Figure 5. On-Resistance Variation with Temperature

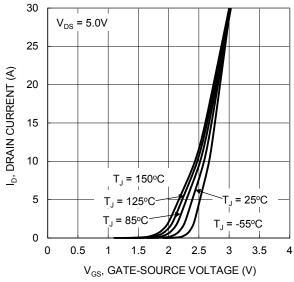


Figure 2. Typical Transfer Characteristic

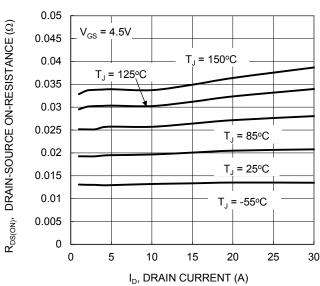


Figure 4. Typical On-Resistance vs Drain Current and Temperature

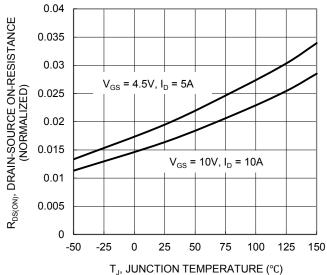


Figure 6.On-Resistance Variation with Temperature





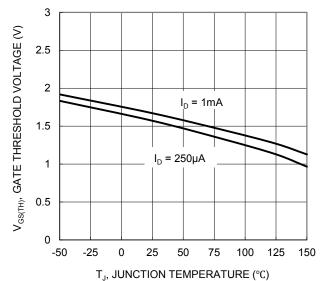
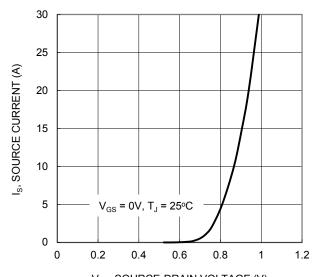


Figure 7. Gate Threshold Variation vs Junction
Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 8. Diode Forward Voltage vs. Current

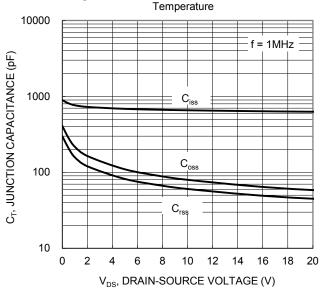


Figure 9. Typical Junction Capacitance

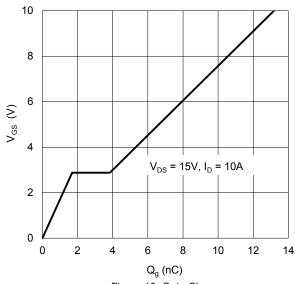


Figure 10. Gate Charge

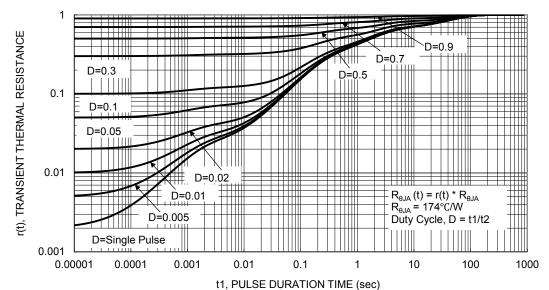


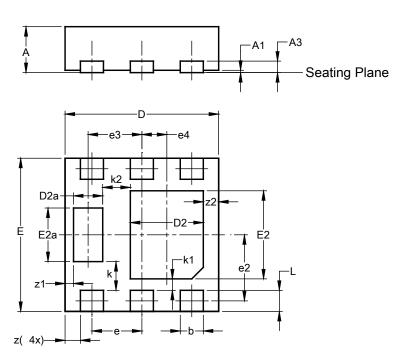
Figure 11. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

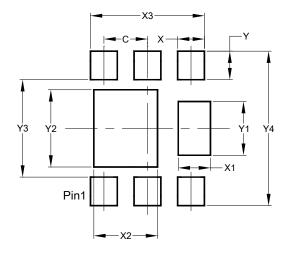


U-DFN2020-6							
(Type F)							
Dim	Min	Min Max Typ					
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	1	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е		0.65 BS	_				
e2		).863 BS					
е3		0.70 BS	_				
e4	(	).325 BS	SC				
k		0.37 BS	_				
k1	0.15 BSC						
k2		0.36 BS	С				
L		0.325					
Z	0.20 BSC						
z1	0.110 BSC						
z2		0.20 BS	С				
All C	)imens	ions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

January 2020

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